

FIG. 1

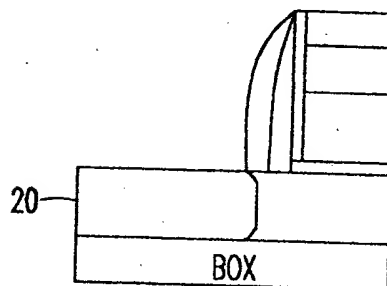
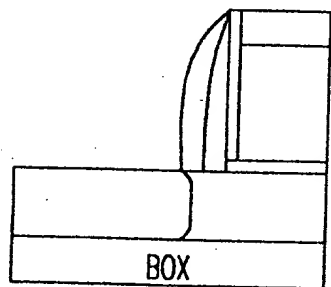


FIG. 2

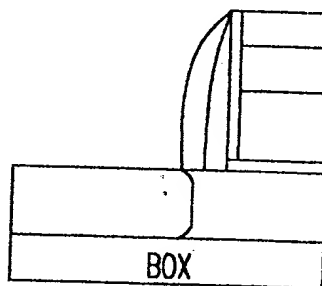
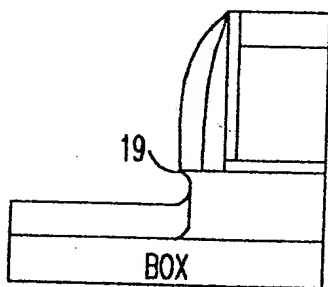


FIG. 3

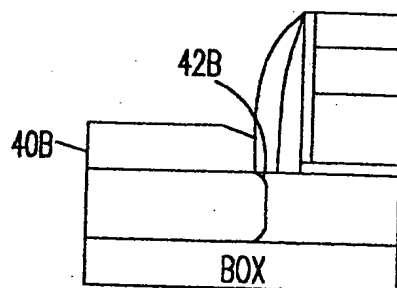
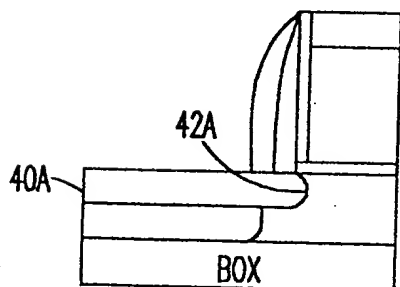


FIG. 4

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TRANSMITTAL OF FORMAL DRAWINGS				Docket No. 00750425AA	
In Re Application Of: H. Park, et al.					
Serial No. 09/924,318	Filing Date 08/08/01	Confirmation No.	Examiner Unassigned	Art Unit 1765	
Invention: METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH SOURCE/DRAIN ELECTRODES FORMED BY IN SITU					

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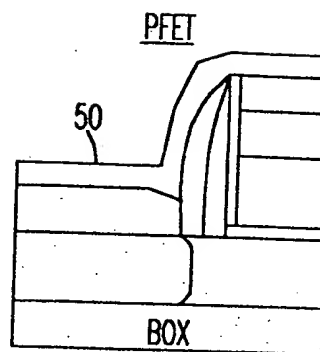
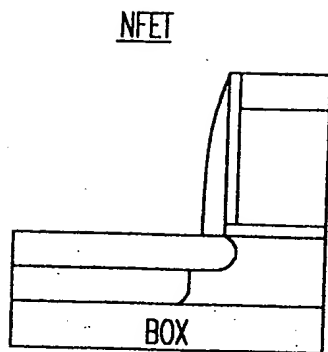


FIG. 5

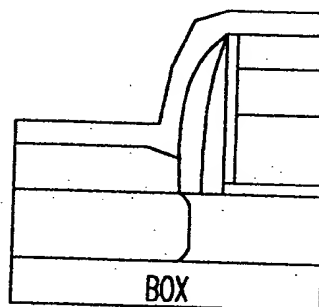
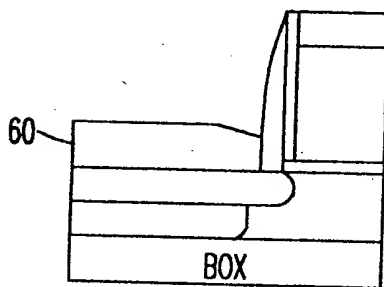


FIG. 6

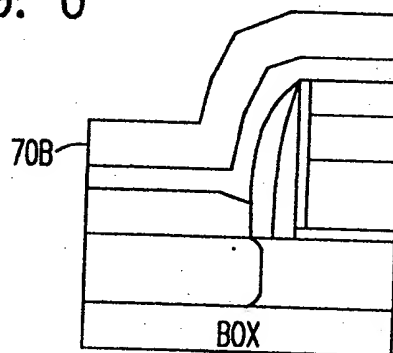
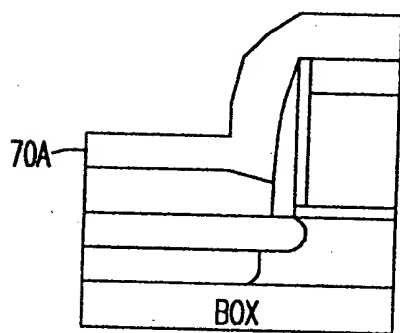


FIG. 7

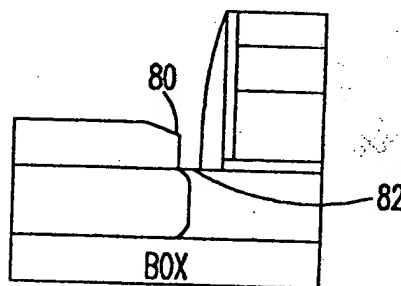
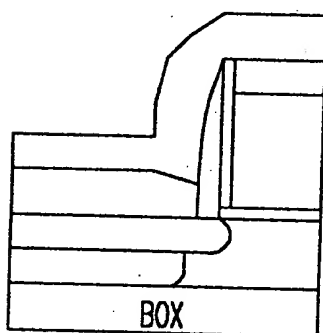


FIG. 8

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00750425AAIn Re Application Of: **H. Park, et al.**

Serial No.

09/924,318

Filing Date

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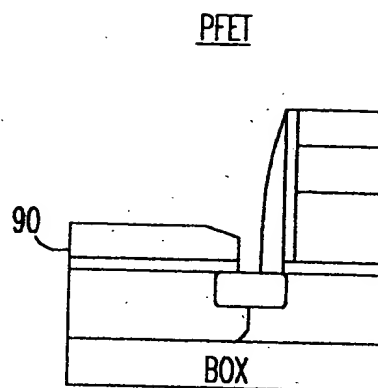
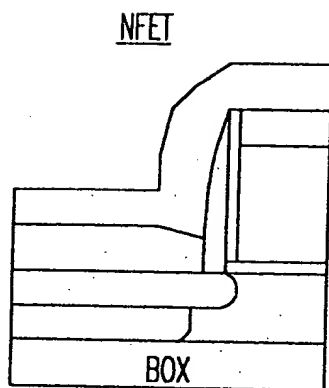


FIG. 9

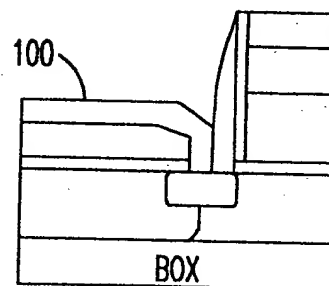
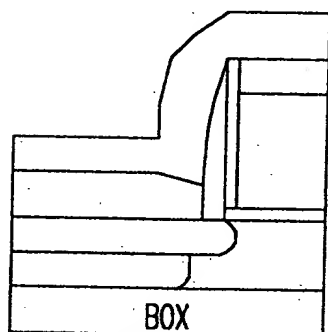


FIG. 10

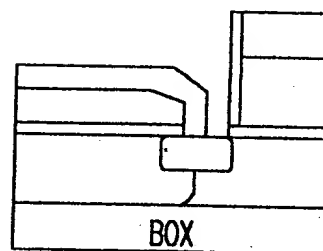
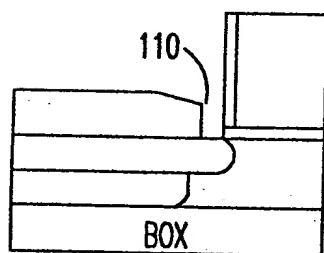


FIG. 11

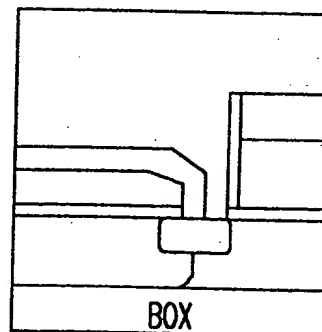
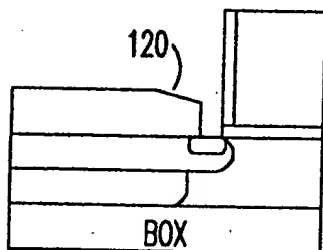


FIG. 12

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In Re Application Of: H. Park, et al.					
Serial No. 09/924,318	Filing Date 08/08/01	Confirmation No.	Examiner Unassigned	Art Unit 1765	
Invention: METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH SOURCE/DRAIN ELECTRODES FORMED BY IN SITU					

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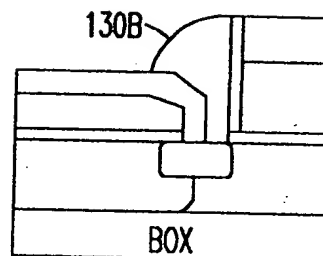
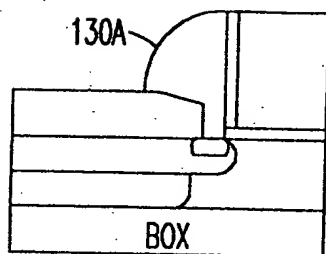


FIG. 13

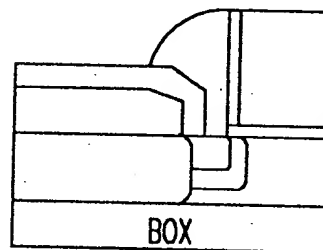
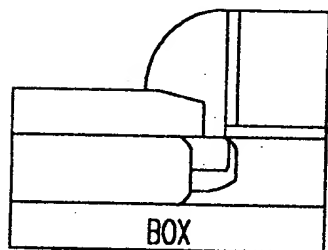


FIG. 14

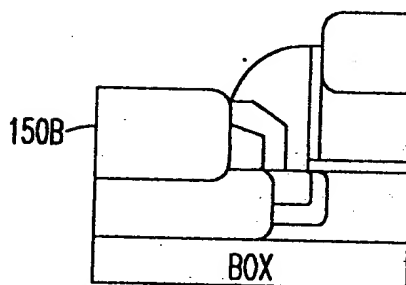
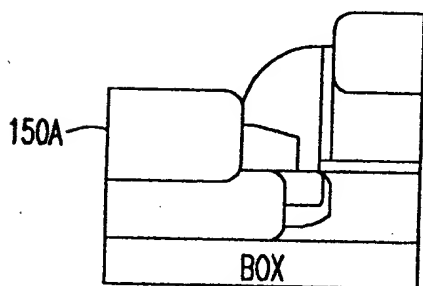


FIG. 15

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00750425AAIn Re Application Of: **H. Park, et al.**Serial No.
09/924,318Filing Date
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1765Invention: **METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH SOURCE/DRAIN
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